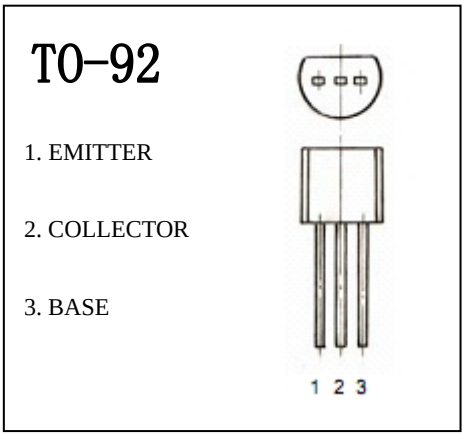
SHENZHEN HAOCHANG SEMICONDUCTOR CO.,LTD.

TO-92 Plastic-Encapsulate Transistors

2SA970 TRANSISTOR(PNP)



MAXIMUM RATINGS(Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
VCBO	Collector-Base Voltage	-120	V
VCEO	Collector-Emitter Voltage	-120	V
VEBO	Emitter-Base Voltage	-5	V
IC	Collector Current	-0.1	A
PC	Collector Power Dissipation	300	mW
Tj	Junction Temperature	150	℃
Tstg	Storag Temperature	-55～150	℃

ELECTRICAL CHARACTERISTICS(Tamb=25℃ unless otherwise specjfied):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR)CBO	IC=-100uA, IE=0	-120			V
Collector-emittre breakdown'voltage	V(BR)CEO	IC=-1mA, IB=0	-120			V
Emitter-base breakdown voltage	V(BR)EBO	IC=-100uA, IC=0	-5			V
Collector cut-off current	ICBO	VCB=-120V, IE=0			-0.1	μA
Emitter cut-off current	IEBO	VEB=-5V，IC=0			-0.1	μA
DC current gain	HFE	Vce=-6V，Ic=-2mA	200		700	
Collector-emitter saturation voltage	VCE(sat)	IC=-10mA,IB=-1mA			-0. 3	V
Base-emitter voltage	VBE	VCE=-6V,IC=-2mA		-0.65		V
Transition frequency	fT	VCE=-6V,IC=-1mA		100		MHz
Collector ouput capacitance	Cob	VCB=-10V,IE=0,f=1MHz		4.0		pF